

## SPECIFICATION OF INFRARED LED CHIP

CN870-30P

[INFRARED]

### 1) Commodity Type and Physical Characteristics.

- |                      |                    |                  |            |
|----------------------|--------------------|------------------|------------|
| 1. Material          | GaAlAs/GaAlAs(DDH) |                  |            |
| 2. Electrode         | Top Side           | P (anode) side   | : Au Alloy |
|                      | Bottom Side        | N (cathode) side | : Au Alloy |
| 3. Electrode Pattern | Fig.1              |                  |            |
| 4. Chip Size         | Fig.2              |                  |            |
| 5. Chip Thickness    | Fig.2              |                  |            |
| 6. Emission Area     | Fig.2              |                  |            |

### 2) Electro-Optical Characteristics

parameters	symbol	condition	min.	typ.	max.	unit
Forward Voltage	V <sub>f</sub>	I <sub>f</sub> =20mA		1.48	1.7	V
Reverse Current	I <sub>r</sub>	V <sub>r</sub> =5V			10	uA
Power Intensity	P <sub>o</sub>	I <sub>f</sub> =20mA	3.0	4.3		mW
Peak Wavelength	λ <sub>P</sub>	I <sub>f</sub> =20mA	860	870	880	nm
Spectral Radiation Bandwidth	Δλ	I <sub>f</sub> =20mA		40		nm
Rise Time	t <sub>r</sub>	I <sub>f</sub> =20mA		15		ns
Full time	t <sub>f</sub>	I <sub>f</sub> =20mA		10		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

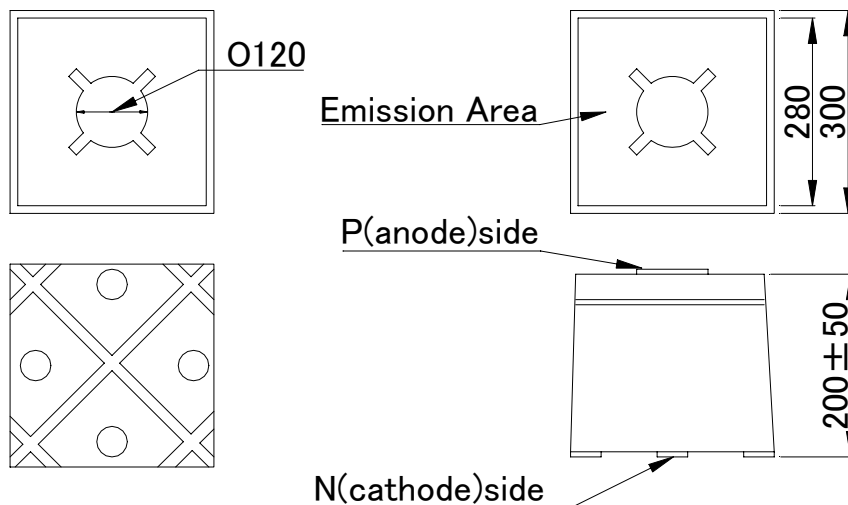


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area